

**1. Material** Substrate GaAs (N Type)  
Epitaxial Layer GaAlAs (P/N Type)

**2. Electrode** N(Cathode) Side Gold Alloy  
P(Anode) Side Gold Alloy

**3. Electro-Optical Characteristics**

Parameter	Symbo	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_F$		1.6	1.7	V	IF=100mA
Reverse Voltage	$V_R$	8			V	IR=10uA
Power	$P_O$	23	30		mW	IF=100mA
Wavelength	$\lambda_P$		940		nm	IF=20mA
	$\Delta\lambda$		45		nm	IF=20mA

※ Note : Power is measured by Sorter E/T system with bare chip.

**4. Mechanical Data**

(a) Emission Area	-----	12.8mil x	12.8mil
(b) Bottom Area	-----	13.8mil x	13.8mil
(c) Bonding Pad	-----	130um	
(d) Chip Thickness	-----	11mil	
(e) Junction Height	-----	6.7mil	

